CY62147EV18
MoBL2™

4-Mbit (256K x 16) Static RAM

Features

- **Very high speed: 45 ns**
- **Wide voltage range: 1.65V–2.25V**
- **Pin-compatible with CY62147DV18**
- **Ultra low standby power**
  - **Typical standby current: 1 μA**
  - **Maximum standby current: 7 μA**
- **Ultra-low active power**
  - **Typical active current: 2 mA @ f = 1 MHz**
- **Ultra low standby power**
- **Easy memory expansion with $\overline{CE}$, and $\overline{OE}$ features**
- **Automatic power-down when deselected**
- **CMOS for optimum speed/power**
- **Available in a 48-ball Pb-free VFBGA package**

Functional Description[1]

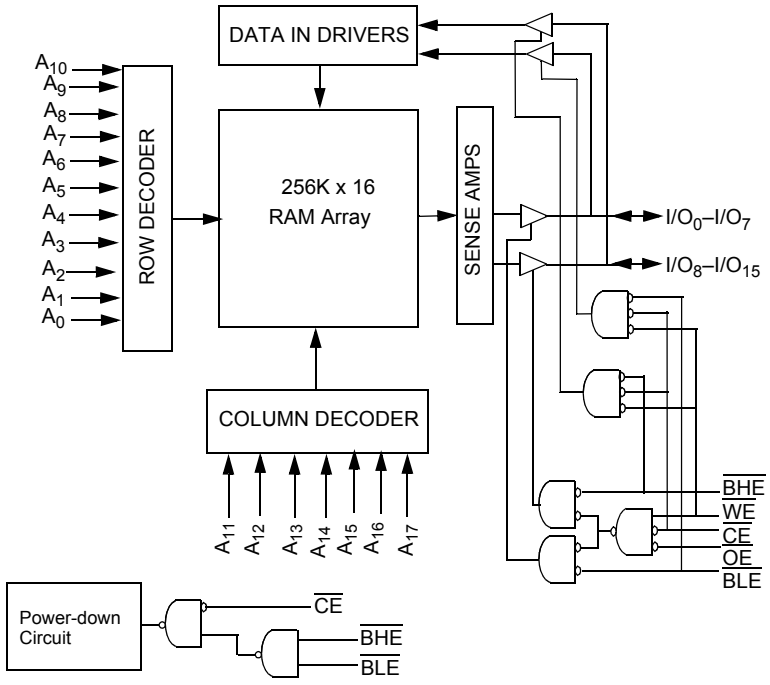
The CY62147EV18 is a high-performance CMOS static RAM organized as 256K words by 16 bits. This device features advanced circuit design to provide ultra-low active current. This is ideal for providing More Battery Life™ (MoBL®) in portable applications such as cellular telephones. The device also has an automatic power-down feature that significantly reduces power consumption when addresses are not toggling. The device can also be put into standby mode reducing power consumption by more than 99% when deselected ($\overline{CE}$ HIGH or both BLE and $\overline{BHE}$ are HIGH). The input/output pins (I/O_0 through I/O_{15}) are placed in a high-impedance state when: deselected ($\overline{CE}$ HIGH), outputs are disabled ($\overline{OE}$ HIGH), both Byte High Enable and Byte Low Enable are disabled ($\overline{BHE}$, BLE HIGH), or during a write operation ($\overline{CE}$ LOW and $\overline{WE}$ LOW).

Writing to the device is accomplished by taking Chip Enable ($\overline{CE}$) and Write Enable ($\overline{WE}$) inputs LOW. If Byte Low Enable (BLE) is LOW, then data from I/O pins (I/O_0 through I/O_7), is written into the location specified on the address pins (A_0 through A_{17}). If Byte High Enable ($\overline{BHE}$) is LOW, then data from I/O pins (I/O_8 through I/O_{15}) is written into the location specified on the address pins (A_0 through A_{17}).

Reading from the device is accomplished by taking Chip Enable ($\overline{CE}$) and Output Enable ($\overline{OE}$) LOW while forcing the Write Enable ($\overline{WE}$) HIGH. If Byte Low Enable (BLE) is LOW, then data from the memory location specified by the address pins will appear on I/O_0 to I/O_7. If Byte High Enable ($\overline{BHE}$) is LOW, then data from memory will appear on I/O_8 to I/O_{15}. See the truth table at the back of this data sheet for a complete description of read and write modes.

The CY62147EV18 is available in a 48-ball VFBGA package.

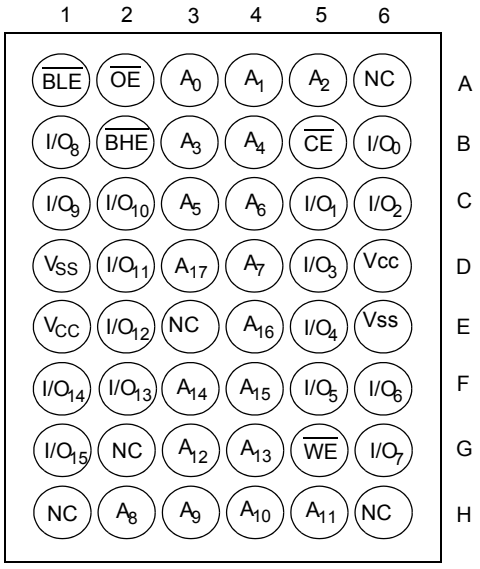
Logic Block Diagram



Note:
1. For best practice recommendations, please refer to the Cypress application note “System Design Guidelines” on http://www.cypress.com.

Pin Configuration[2, 3]

48-ball VFBGA Pinout
Top View



Product Portfolio

Product	V_{CC} Range (V)			Speed (ns)	Power Dissipation					
					Operating I_{CC} (mA)				Standby I_{SB2} (µA)	
					f = 1MHz		f = f_{max}			
	Min.	Typ.[4]	Max.		Typ.[4]	Max.	Typ.[4]	Max.	Typ.[4]	Max.
CY62147EV18-45LL	1.65	1.8	2.25	45	2	2.5	15	20	1	7

Notes:
2. NC pins are not connected on the die.
3. Pins H1, G2, and H6 in the VFBGA package are address expansion pins for 8 Mb, 16 Mb and 32 Mb, respectively.
4. Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at $V_{CC} = V_{CC(typ.)}$, $T_A = 25°C$.

Maximum Ratings

(Above which the useful life may be impaired. For user guidelines, not tested.)

Storage Temperature .....–65°C to + 150°C

Ambient Temperature with Power Applied .....–55°C to + 125°C

Supply Voltage to Ground Potential .....–0.2V to + 2.45V (V_{CCMAX} + 0.2V)

DC Voltage Applied to Outputs in High-Z State[5,6].....–0.2V to 2.45V (V_{CCMAX} + 0.2V)

DC Input Voltage[5,6]..... –0.2V to 2.45V (V_{CCMAX} + 0.2V)

Output Current into Outputs (LOW) ..... 20 mA

Static Discharge Voltage ..... > 2001V (per MIL-STD-883, Method 3015)

Latch-up Current .....> 200 mA

Operating Range

Device	Range	Ambient Temperature	V_{CC} [7]
CY62147EV18	Industrial	–40°C to +85°C	1.65V to 2.25V

Electrical Characteristics (Over the Operating Range)

Parameter	Description	Test Conditions		45 ns			Unit
				Min.	Typ.[4]	Max.	
V_{OH}	Output HIGH Voltage	I_{OH} = –0.1 mA	V_{CC} = 1.65V	1.4			V
V_{OL}	Output LOW Voltage	I_{OL} = 0.1 mA	V_{CC} = 1.65V			0.2	V
V_{IH}	Input HIGH Voltage	V_{CC} =1.65V to 2.25V		1.4		V_{CC}+ 0.2V	V
V_{IL}	Input LOW Voltage	V_{CC} =1.65V to 2.25V		–0.2		0.4	V
I_{IX}	Input Leakage Current	GND ≤ V_I ≤ V_{CC}		–1		+1	µA
I_{OZ}	Output Leakage Current	GND ≤ V_O ≤ V_{CC}, Output Disabled		–1		+1	µA
I_{CC}	V_{CC} Operating Supply Current	f = f_{MAX} = 1/t_{RC}	$V_{CC(max)}$=2.25V I_{OUT} = 0 mA CMOS levels		15	20	mA
		f = 1 MHz	$V_{CC(max)}$=2.25V		2	2.5	mA
I_{SB1}	Automatic CE Power-down Current — CMOS Inputs	$\overline{CE}$ ≥ V_{CC}–0.2V, V_{IN}≥V_{CC} – 0.2V, V_{IN} ≤ 0.2V) f = f_{MAX} (Address and Data Only), f = 0 ($\overline{OE}$, $\overline{WE}$, $\overline{BHE}$ and $\overline{BLE}$)	$V_{CC(max)}$=2.25V		1	7	µA
I_{SB2}	Automatic CE Power-down Current — CMOS Inputs	$\overline{CE}$ ≥ V_{CC} – 0.2V, V_{IN} ≥ V_{CC} – 0.2V or V_{IN} ≤ 0.2V, f = 0	$V_{CC(max)}$=2.25V		1	7	µA

Capacitance (for all Packages) [8]

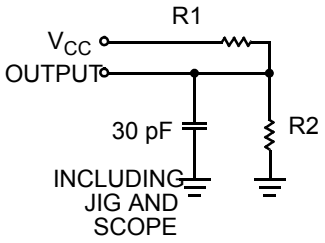
Parameter	Description	Test Conditions	Max.	Unit
C_{IN}	Input Capacitance	T_A = 25°C, f = 1 MHz, V_{CC} = $V_{CC(typ)}$	10	pF
C_{OUT}	Output Capacitance		10	pF

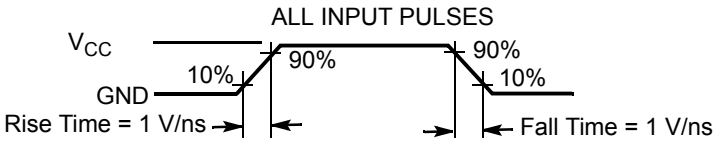
Note:
5. $V_{IL(min.)}$ = –2.0V for pulse durations less than 20 ns.
6. $V_{IH(max)}$=V_{CC}+0.5V for pulse durations less than 20 ns.
7. Full device AC operation assumes a minimum of 100 µs ramp time from 0 to V_{cc}(min) and 200 µs wait time after V_{cc} stabilization.
8. Tested initially and after any design or process changes that may affect these parameters.

Thermal Resistance

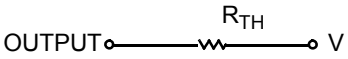
Parameter	Description	Test Conditions	VFBGA Package	Unit
Θ_{JA}	Thermal Resistance (Junction to Ambient)[8]	Still Air, soldered on a 3 × 4.5 inch, two-layer printed circuit board	75	°C/W
Θ_{JC}	Thermal Resistance (Junction to Case)[8]		10	°C/W

AC Test Loads and Waveforms





Equivalentto: THEVENIN EQUIVALENT

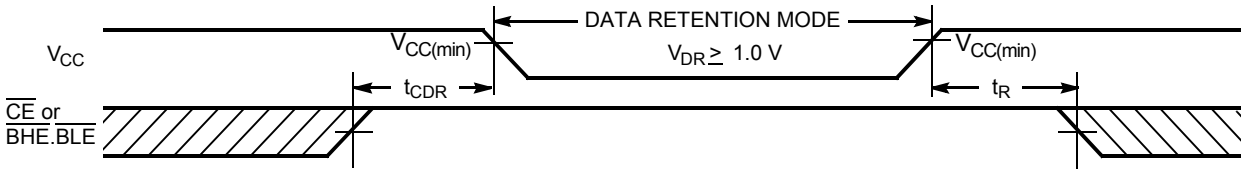


Parameters	1.80V	Unit
R1	13500	Ω
R2	10800	Ω
R_{TH}	6000	Ω
V_{TH}	0.80	V

Data Retention Characteristics (Over the Operating Range)

Parameter	Description	Conditions	Min.	Typ.[4]	Max.	Unit
V_{DR}	V_{CC} for Data Retention		1.0			V
I_{CCDR}	Data Retention Current	V_{CC}= 1.0V $\overline{CE} \geq V_{CC} - 0.2V$, $V_{IN} \geq V_{CC} - 0.2V$ or $V_{IN} \leq 0.2V$		0.5	3	µA
t_{CDR}[7]	Chip Deselect to Data Retention Time		0			ns
t_R[9]	Operation Recovery Time		t_{RC}			ns

Data Retention Waveform[10]



Notes:
9. Full device operation requires linear V_{CC} ramp from V_{DR} to $V_{CC(min.)} \geq 100$ µs or stable at $V_{CC(min.)} \geq 100$µs.
10. $\overline{BHE}.\overline{BLE}$ is the AND of both $\overline{BHE}$ and $\overline{BLE}$. Chip can be deselected by either disabling the chip enable signals or by disabling both $\overline{BHE}$ and $\overline{BLE}$.

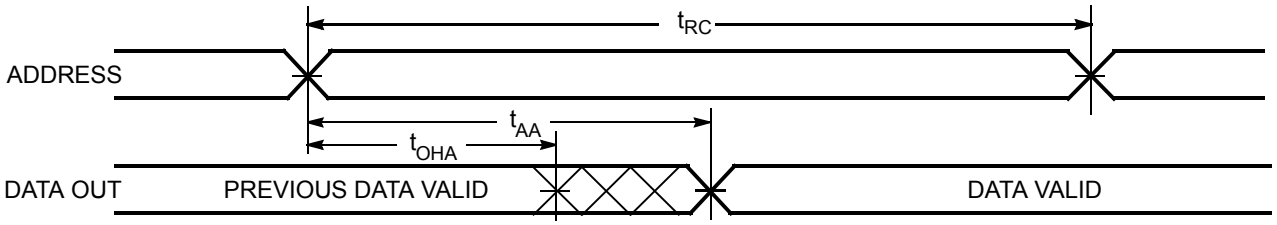
Switching Characteristics (Over the Operating Range) [11]

Parameter	Description	45 ns		Unit
		Min.	Max.	
Read Cycle				
t_{RC}	Read Cycle Time	45		ns
t_{AA}	Address to Data Valid		45	ns
t_{OHA}	Data Hold from Address Change	10		ns
t_{ACE}	$\overline{CE}$ LOW to Data Valid		45	ns
t_{DOE}	$\overline{OE}$ LOW to Data Valid		22	ns
t_{LZOE}	$\overline{OE}$ LOW to LOW Z[12]	5		ns
t_{HZOE}	$\overline{OE}$ HIGH to High Z[12, 13]		18	ns
t_{LZCE}	$\overline{CE}$ LOW to Low Z[12]	10		ns
t_{HZCE}	$\overline{CE}$ HIGH to High Z[12, 13]		18	ns
t_{PU}	$\overline{CE}$ LOW to Power-up	0		ns
t_{PD}	$\overline{CE}$ HIGH to Power-down		45	ns
t_{DBE}	$\overline{BLE}/\overline{BHE}$ LOW to Data Valid		45	ns
t_{LZBE}	$\overline{BLE}/\overline{BHE}$ LOW to Low Z[12]	10		ns
t_{HZBE}	$\overline{BLE}/\overline{BHE}$ HIGH to HIGH Z[12, 13]		18	ns
Write Cycle[14]				
t_{WC}	Write Cycle Time	45		ns
t_{SCE}	$\overline{CE}$ LOW to Write End	35		ns
t_{AW}	Address Set-up to Write End	35		ns
t_{HA}	Address Hold from Write End	0		ns
t_{SA}	Address Set-up to Write Start	0		ns
t_{PWE}	$\overline{WE}$ Pulse Width	35		ns
t_{BW}	$\overline{BLE}/\overline{BHE}$ LOW to Write End	35		ns
t_{SD}	Data Set-up to Write End	25		ns
t_{HD}	Data Hold from Write End	0		ns
t_{HZWE}	$\overline{WE}$ LOW to High-Z[12, 13]		18	ns
t_{LZWE}	$\overline{WE}$ HIGH to Low-Z[12]	10		ns

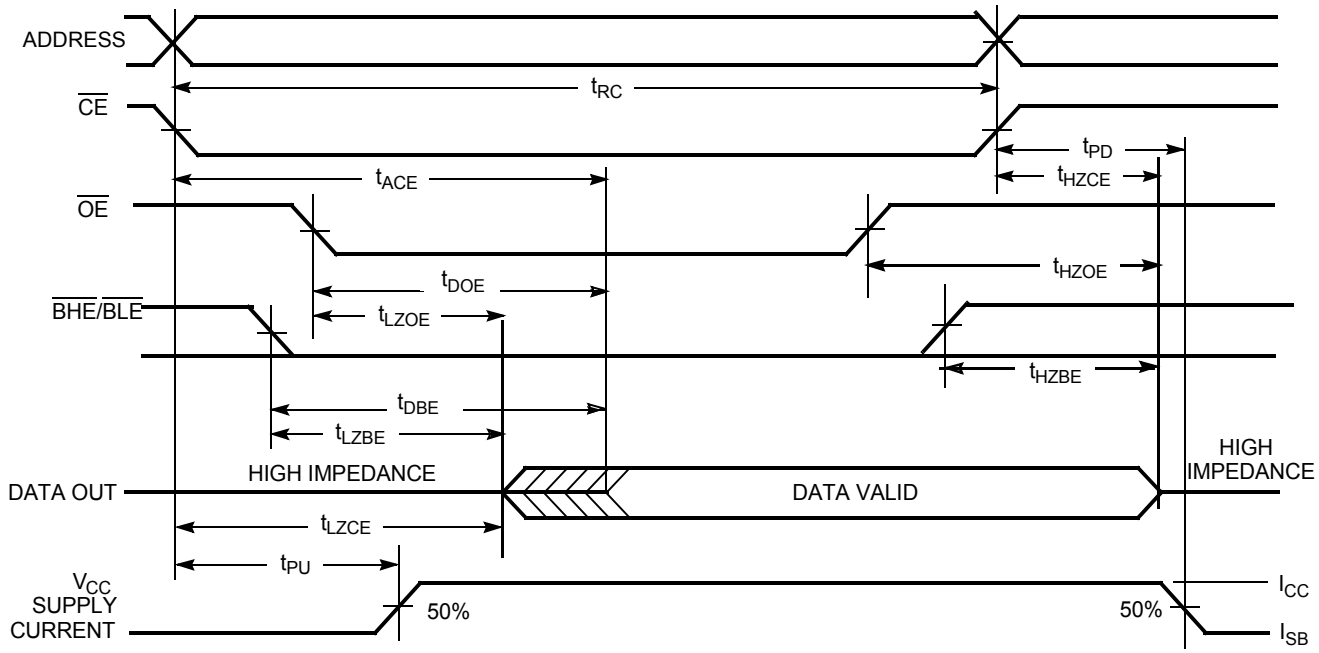
Notes:
11. Test conditions for all parameters other than three-state parameters assume signal transition time of 1V/ns or less, timing reference levels of $V_{CC(typ)}/2$, input pulse levels of 0 to $V_{CC(typ.)}$, and output loading of the specified I_{OL}/I_{OH} as shown in the “AC Test Loads and Waveforms” section.
12. At any given temperature and voltage condition, t_{HZCE} is less than t_{LZCE}, t_{HZBE} is less than t_{LZBE}, t_{HZOE} is less than t_{LZOE}, and t_{HZWE} is less than t_{LZWE} for any given device.
13. t_{HZOE}, t_{HZCE}, t_{HZBE}, and t_{HZWE} transitions are measured when the outputs enter a high impedence state
14. The internal Write time of the memory is defined by the overlap of $\overline{WE}$, $\overline{CE}$ = V_{IL}, $\overline{BHE}$ and/or $\overline{BLE}$ = V_{IL}. All signals must be ACTIVE to initiate a write and any of these signals can terminate a write by going INACTIVE. The data input set-up and hold timing should be referenced to the edge of the signal that terminates the write.

Switching Waveforms

Read Cycle 1 (Address Transition Controlled)[15, 16]



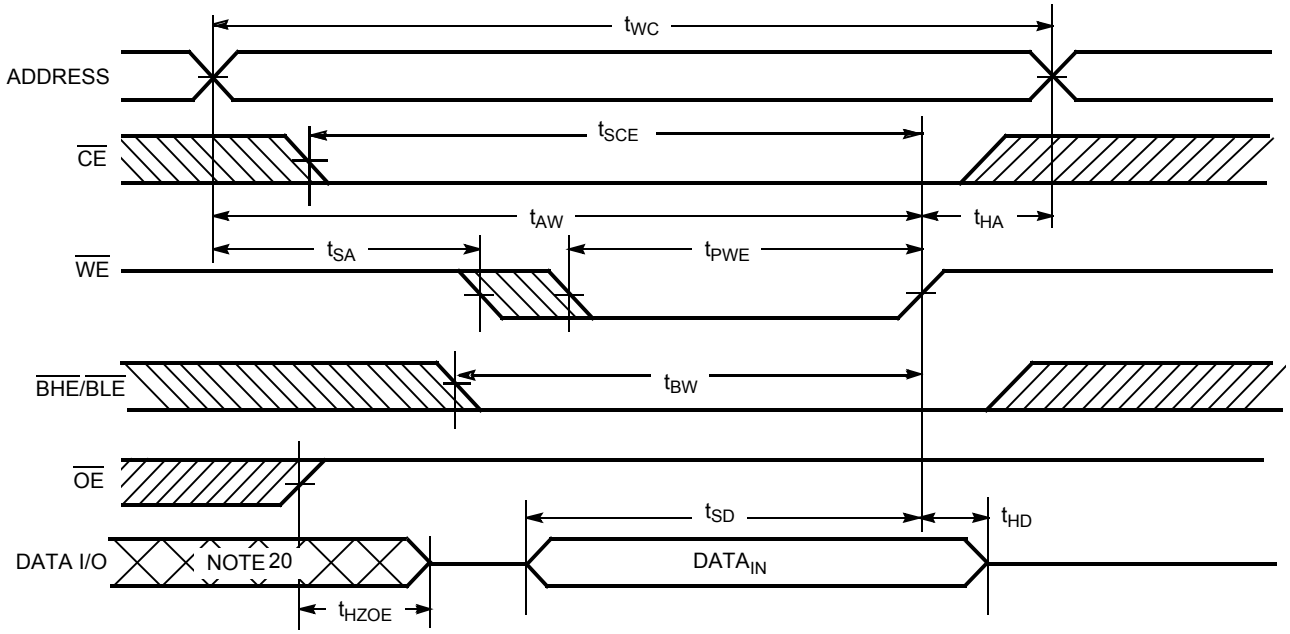
Read Cycle No. 2 ($\overline{OE}$ Controlled)[16, 17]



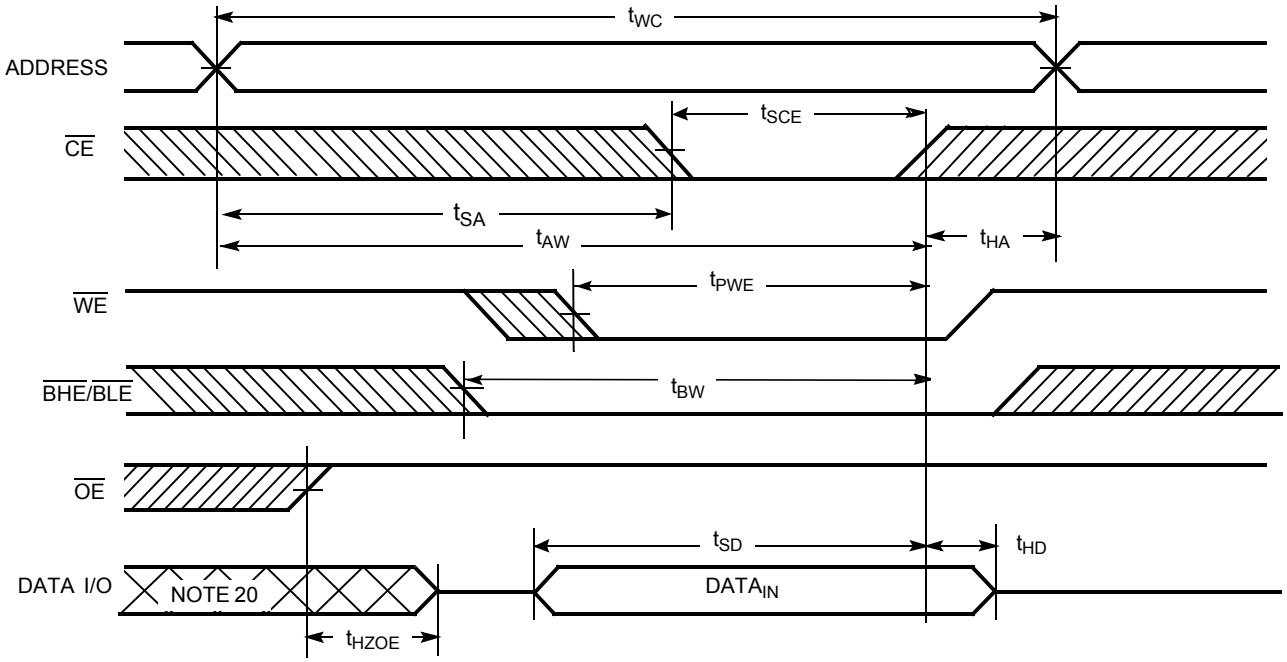
Notes:
15. The device is continuously selected. $\overline{OE}$, $\overline{CE}$ = V_{IL}, $\overline{BHE}$ and/or $\overline{BLE}$ = V_{IL}.
16. $\overline{WE}$ is HIGH for read cycle.
17. Address valid prior to or coincident with $\overline{CE}$ and $\overline{BHE}$, $\overline{BLE}$ transition LOW.

Switching Waveforms (continued)

Write Cycle No. 1 (WE Controlled)[14, 18, 19]



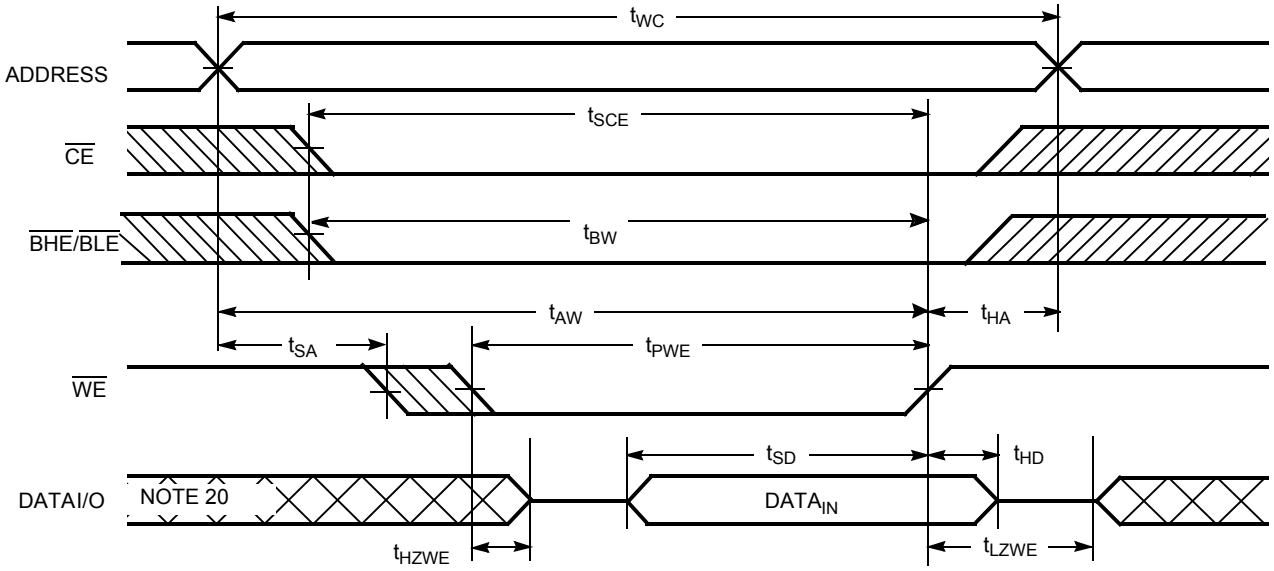
Write Cycle No. 2 (CE Controlled)[14, 18, 19]



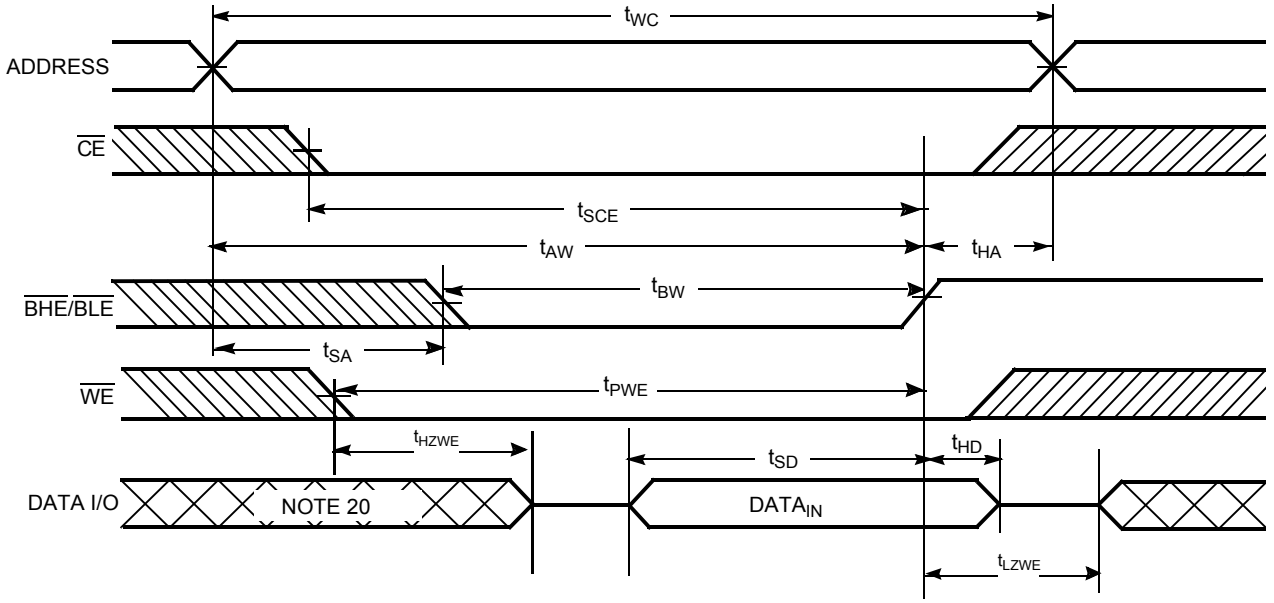
Notes:
18. Data I/O is high impedance if $\overline{OE}$ = V_{IH}.
19. If $\overline{CE}$ goes HIGH simultaneously with $\overline{WE}$ = V_{IH}, the output remains in a high-impedance state.
20. During this period, the I/Os are in output state and input signals should not be applied.

Switching Waveforms (continued)

Write Cycle No. 3 (WE Controlled, OE LOW)[19]



Write Cycle No. 4 (BHE/BLE Controlled, OE LOW)[19]



Truth Table

$\overline{CE}$	$\overline{WE}$	$\overline{OE}$	$\overline{BHE}$	$\overline{BLE}$	Inputs/Outputs	Mode	Power
H	X	X	X	X	High Z	Deselect/Power-down	Standby (I_{SB})
L	X	X	H	H	High Z	Deselect/Power-down	Standby (I_{SB})
L	H	L	L	L	Data Out (I/O_O–I/O_{15})	Read	Active (I_{CC})
L	H	L	H	L	Data Out (I/O_O–I/O_7); I/O_8–I/O_{15} in High Z	Read	Active (I_{CC})
L	H	L	L	H	Data Out (I/O_8–I/O_{15}); I/O_0–I/O_7 in High Z	Read	Active (I_{CC})
L	H	H	L	L	High Z	Output Disabled	Active (I_{CC})
L	H	H	H	L	High Z	Output Disabled	Active (I_{CC})
L	H	H	L	H	High Z	Output Disabled	Active (I_{CC})
L	L	X	L	L	Data In (I/O_O–I/O_{15})	Write	Active (I_{CC})
L	L	X	H	L	Data In (I/O_O–I/O_7); I/O_8–I/O_{15} in High Z	Write	Active (I_{CC})
L	L	X	L	H	Data In (I/O_8–I/O_{15}); I/O_0–I/O_7 in High Z	Write	Active (I_{CC})

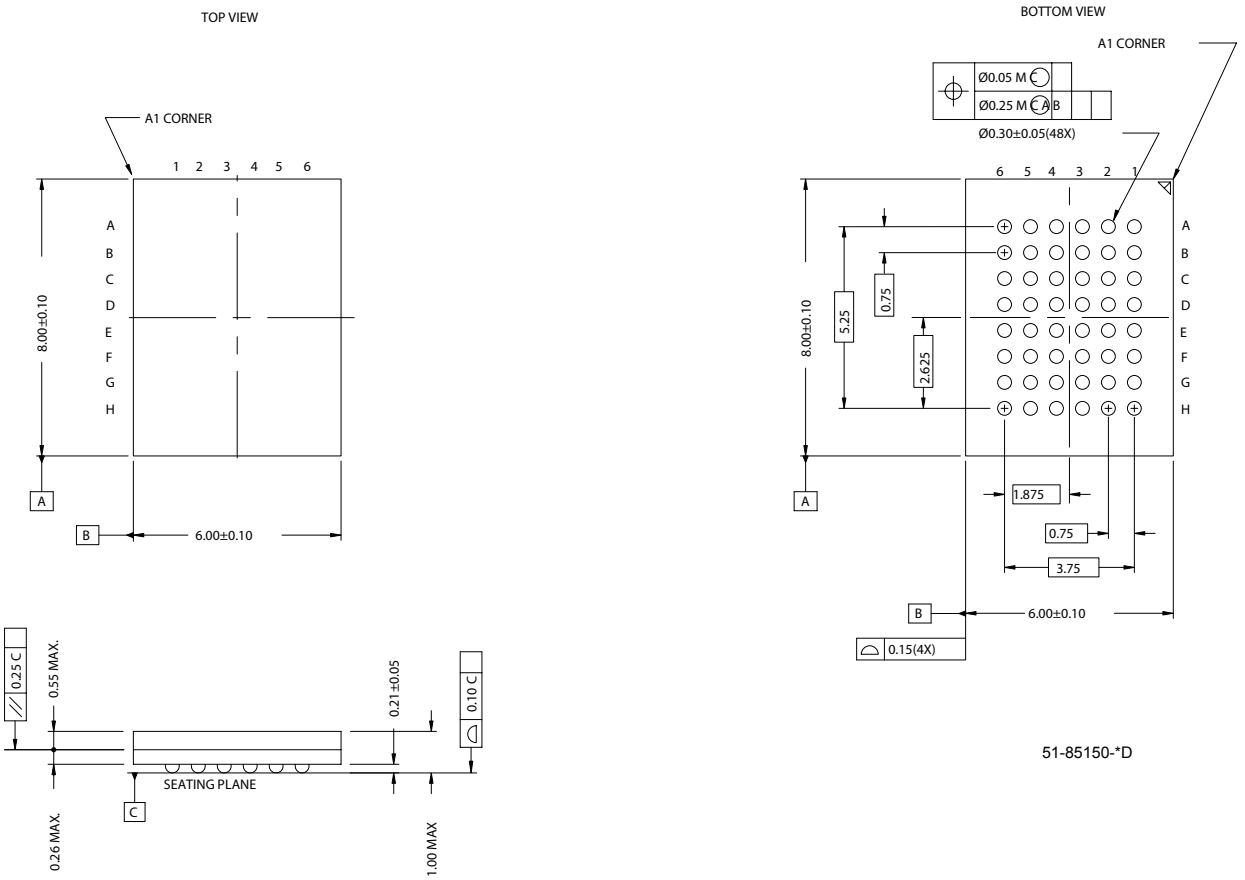
Ordering Information

Speed (ns)	Ordering Code	Package Diagram	Package Type	Operating Range
45	CY62147EV18LL-45BVXI	51-85150	48-ball Very Fine Pitch Ball Grid Array Pb-Free	Industrial

Please contact your local Cypress sales representative for availability of other parts

Package Diagram

48-pin VFBGA (6 x 8 x 1 mm) (51-85150)



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Document History Page

Document Title:CY62147EV18 MoBL2™ 4-Mbit (256K x 16) Static RAM Document Number: 38-05441				
REV.	**ECN NO.**	**Issue Date**	**Orig. of Change**	**Description of Change**
**	201580	01/08/04	AJU	New Data Sheet
*A	247009	See ECN	SYT	Changed from Advance Information to Preliminary Moved Product Portfolio to Page 2 Changed V_{CCMax} from 2.20 to 2.25 V Changed V_{CC} stabilization time in footnote #8 from 100 μs to 200 μs Removed Footnote #15 (t_{LZBE}) from Previous Revision Changed I_{CCDR} from 2.0 μA to 2.5 μA Changed typo in Data Retention Characteristics (t_R) from 100 μs to t_{RC} ns Changed t_{OHA} from 6 ns to 10 ns for both 35 ns and 45 ns Speed Bin Changed t_{HZOE}, t_{HZBE}, t_{HZWE} from 12 to 15 ns for 35 ns Speed Bin and 15 to 18 ns for 45 ns Speed Bin Changed t_{SCE} and t_{BW} from 25 to 30 ns for 35 ns Speed Bin and 40 to 35 ns for 45 ns Speed Bin Changed t_{HZCE} from 12 to 18 ns for 35 ns Speed Bin and 15 to 22 ns for 45 ns Speed Bin Changed t_{SD} from 15 to 18 ns for 35 ns Speed Bin and 20 to 22 ns for 45 ns Speed Bin Changed t_{DOE} from 15 to 18 ns for 35 ns Speed Bin Changed Ordering Information to include Pb-Free Packages
*B	414820	See ECN	ZSD	Changed from Preliminary to Final Changed the address of Cypress Semiconductor Corporation on Page #1 from “3901 North First Street” to “198 Champion Court” Removed 35ns Speed Bin Removed “L” version of CY62147EV18 Changed ball E3 from DNU to NC Changed I_{CC} (Typ) value from 1.5 mA to 2 mA at f=1 MHz Changed I_{CC} (Max) value from 2 mA to 2.5 mA at f=1 MHz Changed I_{CC} (Typ) value from 12 mA to 15 mA at f=f_{max} Changed I_{SB1} and I_{SB2} Typ. values from 0.7 μA to 1 μA and Max. values from 2.5 μA to 7 μA. Extended undershoot limit to -2V in footnote #5 Changed I_{CCDR} Max. from 2.5 μA to 3 μA. Added I_{CCDR} typical value. Changed t_{LZOE} from 3 ns to 5 ns Changed t_{LZCE}, t_{LZBE} and t_{LZWE} from 6 ns to 10 ns Changed t_{HZCE} from 22 ns to 18 ns Changed t_{PWE} from 30 ns to 35 ns. Changed t_{SD} from 22 ns to 25 ns. Updated the package diagram 48-pin VFBGA from *B to *D Updated the ordering information table and replaced Package Name column with Package Diagram